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School on Synchrotron and FEL Based Methods and their Multi-Disciplinary Applications

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ARPES

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Angle resolved photoemission: Interacting electrons

Part III

Papers: S. Hüfner et al., J. Electron Spectroscopy Rel. Phenom. 100 (1999)
A. Damascelli et al., Rev. Modern Phys. (2005)
F. Reinert et al., New J. Phys. 7 (2005)
X.J. Zhou et al., J. Electron Spectroscopy Rel. Phenom. 126 (2002)

Thanks to: A. Damascelli, Z.X. Shen, R. Claessen, Ph. Hofmann and E. Rotemberg from whose I have taken slides and figures

Outline

- Interacting electrons: many-body physics
- Single particle spectral density function $A(k, \omega)$
- The self-energy
- The "kinky" physics: electron-phonon interactions
- 1D System: Luttinger liquid. Spinon and holon dispersion
- Mott-Hubbard insulator
- Fullerenes

Interaction effects between electrons: "Many-body Physics"

Many body effects are due to the interactions between the electrons and each other, or with excitations inside the crystal :

1) A "many-body" problem: intrinsically hard to calculate and understand

2) Responsible for many surprising phenomena: *Superconductivity, Magnetism, Density Waves,*



Interacting Electrons: many-body physics

$$\begin{split} \sum_{j=1}^{N} A(r_j) \cdot p_j &= A \cdot p \\ I(E_{kin}) &= \frac{2e^2 \pi}{m^2 \hbar} \sum_{f} \left| \langle N, f | A \cdot p | N, i \rangle \right|^2 \rho(E_f^N) \delta(E_f^N - E_i^N - h\nu) \\ I(E_{kin}) &= \sum_{f} \left| M_{fi} \right|^2 \rho(E_f^N) \delta(E_f^N - E_i^N - h\nu) \end{split}$$

The final state relevant for photoemission must contain a free electron with wave vector \mathbf{k} and energy E_{kin} .

$$I(E_{kin}) = \frac{2e^{2}\pi}{m^{2}\hbar} \sum_{x} \left| \langle k, N - 1, x | A \cdot p | N, i \rangle \right|^{2} \rho(E_{x}^{N-1}) \rho(E_{kin}) \delta(E_{kin} + E_{x}^{N-1} - E_{i}^{N} - h\nu)$$

Now the sum is over all the possible final excited states x of the (N-1)-electrons system left behind by the photoelectron. The essential step in simplifying this expression consists in the factorization of the final state wave function lk, N-1, x) as the product of the photoelectron ϕ_k and the ϕ_x (N-1) electrons wave functions.

In second quantization $|k, N - 1, x\rangle \approx \phi_k \phi_k (N - 1) = c_k^+ |N - 1, x\rangle$

This involves two assumptions:

- 1) Sudden approx.: The photoelectron decuples immediately from the photohole left behind and carries no information on the relaxation of the (N-1) system
- 2) We neglect inelastic losses of the photoelectron on its travel inside the crystal

$$I(E_{kin}) = \frac{2e^{2}\pi}{m^{2}\hbar} \sum_{j=1}^{N} |M_{k,kj}|^{2} \sum_{x} |\langle N-1, x|c_{kj}|N, i\rangle|^{2} \rho(E_{x}^{N-1}) \rho(E_{kin}) \delta(E_{kin} + E_{x}^{N-1} - E_{i}^{N} - h\nu)$$

where

$$|\mathbf{N}, \mathbf{i}\rangle = \frac{1}{N} c_{kj}^{\dagger} c_{kj} |\mathbf{N}, \mathbf{i}\rangle \qquad \mathbf{M}_{k,kj} = \frac{1}{N} c_k A(r_j) p_j c_{kj}^{\dagger} = \frac{1}{N} \langle \mathbf{k} | A(r_j) p_j | kj\rangle$$

Transition probability for interacting electrons

$$I(E_{kin}) = \frac{2e^{2}\pi}{m^{2}\hbar} \sum_{j=1}^{N} |M_{k,kj}|^{2} \sum_{x} |\langle N - 1, x | c_{kj} | N, i \rangle^{2} \rho(E_{kin}) \rho(E_{kin}) \delta(E_{kin} + E_{x}^{N-1} - E_{i}^{N} - h\nu)$$

c_{ki} destroys an electron with momentum kj from the initial state IN,i)

 $|N-1,x\rangle$ is an eigenstate of the (N-1) Hamiltonian, while the (N-1) wave function $c_{ki}|N,i\rangle$ is not

We can write
$$E_i^N - E_x^{N-1} = (E_i^N - E_0^{N-1}) - (E_x^{N-1} - E_0^{N-1}) = \mathcal{E}_0^i - \Delta \mathcal{E}_x$$

Interpretation: The photon absorption suddenly creates an (N-1)-electron state $c_{kj}|N,i$) that is not an eigenstate of the (N-1) Hamiltonian (frozen state). The spectrum is the projection of this frozen states over the "fully relaxed" eigenstates $|N-1,x\rangle$ of the (N-1) Hamiltonian. We call "fundamental peak" (or "elastic peak", or "coherent peak") the transition leaving the (N-1)-system in the ground state $|N-1,0\rangle$ that correspond to a photoelectron with kinetic energy $E_{kin} = (E_i^N - E_0^{N-1}) + hv = \varepsilon_0^i + hv$ The spectrum also exhibits peaks at lower kinetic energies by quantities $-\Delta\varepsilon_x$ when the system is left in an excited $|N-1,x\rangle$ state.

Interacting electrons



Kinetic Energy







Still no information on the lifetime of the states (width of the peaks)

A bit of math and the quasi-particles

It is useful to introduce the one-electron removal Green function formalism:

$$G(kj,\omega j) = \sum_{x} \frac{\left| \langle N-1, x | c_{kj} | N, i \rangle \right|^{2}}{\omega j - E_{x}^{N-1} + E_{i}^{N} - i\eta} \qquad \eta \text{ can be infinitesimally small}$$

 c_{kj} destroys an electron with momentum kj and energy ωj from the initial state IN,i)

... and the corresponding spectral density function $A(kj,\omega j)=(1/\pi)ImG(kj,\omega j)$ In the limit $\eta \rightarrow 0$:

$$A(kj,\omega j) = \frac{1}{\pi} \sum_{x} \left| \langle N - 1, x | c_{kj} | N, i \rangle \right|^2 \delta \left(\omega j - E_x^{N-1} + E_i^N \right) = \frac{1}{\pi} \operatorname{Im} G(kj,\omega j)$$

Comparing to:

$$I(E_{kin}) = \frac{2e^{2}\pi}{m^{2}\hbar} \sum_{j=1}^{N} |M_{k,kj}|^{2} \sum_{x} |\langle N - 1, x | c_{kj} | N, i \rangle|^{2} \rho(E_{x}^{N-1}) \rho(E_{kin}) \delta(E_{kin} + E_{x}^{N-1} - E_{i}^{N} - h\nu)$$

We have $I(E_{kin}) = \frac{2e^{2}\pi^{2}}{m^{2}\hbar} \sum_{j=1}^{N} |M_{k,kj}|^{2} A(kj, \omega j)$

Where A(kj, ωj) $\neq 0$ only when $\omega j = h\nu - E_{kin} = \left| E_i^N - E_x^{N-1} \right|$

Rewriting in terms of the electron binding energy ω , considering the momentum conservation and including the Fermi-Dirac distribution:



This is the most important result: in the sudden approx. the photoemission spectrum is proportional to the single particle spectral density function $A(k, \omega)$

This relationship has been obtained in the limit $\eta \rightarrow 0$ (η is the peak width), i.e. the peaks are Dirac's δ . It can be extended to "real systems" where the width Γ is finite.

$$G(k,\omega) = \sum_{x} \frac{\left| \langle N - 1, x | c_k | N, i \rangle \right|^2}{\omega - E_x^{N-1} + E_i^N - i\Gamma}$$
$$A(k,\omega) = \frac{1}{\pi} \operatorname{Im} G(k,\omega) = \frac{\Gamma}{\pi} \sum_{x} \frac{\left| \langle N - 1, x | c_k | N, i \rangle \right|^2}{(\omega - E_x^{N-1} + E_i^N)^2 + \Gamma^2}$$

Quasi-particle: when one hole is added adiabatically forming an (N-1)-electron system the coulomb interaction is screened by the formation of an electron cloud around the hole. At equilibrium, the hole+the screening cloud is a quasi-particle.

An eigenstate |N-1, x| of the (N-1)-electron system can be obtained by adding a quasi-particle to the N-electron system (quasi-particle state).

If instead we suddenly simply add a bare hole of momentum k (or we remove an electron of momentum k) we obtain the state $c_k | N, i \rangle$, that in general is not an eigenstate of the (N-1)-system, but it will have a finite overlap with the corresponding quasi-particle state.

The spectral density function $A(k, \omega)$ gives the probability that the original system plus the bare hole will be found in an exact eigenstate of the (N-1)-system



$$G(k,\omega) = \frac{\left| \langle N - 1, i | c_k | N, i \rangle \right|^2}{\omega - \varepsilon(k) - i\Gamma} + \sum_{x \neq i} \frac{\left| \langle N - 1, x | c_k | N, i \rangle \right|^2}{\omega - \varepsilon_x(k) - i\Gamma} = G_{coh}(k,\omega) + G_{incoh}(k,\omega)$$

$$A(k,\omega) = -\frac{1}{\pi} \operatorname{Im} G(k,\omega) = \frac{\Gamma}{\pi} \frac{|\langle N-1,i|c_{k}|N,i\rangle|^{2}}{(\omega-\varepsilon(k))^{2}+\Gamma^{2}} + \frac{\Gamma}{\pi} \sum_{x\neq i} \frac{|\langle N-1,x|c_{k}|N,i\rangle|^{2}}{(\omega-\varepsilon_{x}(k))^{2}+\Gamma^{2}}$$
$$= A(k,\omega)_{\operatorname{coh.}} + A(k,\omega)_{\operatorname{incoh}}$$

Where $\varepsilon(k)$ is the quasi-particle energy referred to the Fermi level $\mu=0$

As $\varepsilon(\mathbf{k}) \rightarrow \mu$, $\Gamma \propto (\varepsilon - \mu)^2 \rightarrow 0$

The quasi-particle is well-defined only at (or very close to) the Fermi level, where its lifetime $1/\Gamma \rightarrow \infty$



$$A(k,\omega) = \frac{\Gamma}{\pi} \frac{Z_k}{(\omega - \varepsilon(k))^2 + \Gamma^2} + \frac{\Gamma}{\pi} \sum_{x \neq i} \frac{|\langle N - 1, x | c_k | N, i \rangle|^2}{(\omega - \varepsilon_x(k))^2 + \Gamma^2} = A(k,\omega)_{\text{coh.}} + A(k,\omega)_{\text{incoh}}$$





1.0







ARPES: FWHM and Inverse Lifetime

 $\begin{array}{l} \text{FWHM of an} \\ \text{ARPES peak} \end{array} \right\} \Gamma = \frac{\frac{\Gamma_i}{|v_{i\perp}|} + \frac{\Gamma_f}{|v_{f\perp}|}}{\left|\frac{1}{v_{i\perp}} \left[1 - \frac{mv_{i\parallel}\sin^2\vartheta}{\hbar k_{\parallel}}\right] - \frac{1}{v_{f\perp}} \left[1 - \frac{mv_{f\parallel}\sin^2\vartheta}{\hbar k_{\parallel}}\right]} \right| \end{array}$



1) if
$$E_i \simeq E_F$$

 $\rightarrow \Gamma_i \longrightarrow 0 \rightarrow \Gamma \propto \Gamma_f$
2) if $|v_{i\perp}| \simeq 0$
 $\rightarrow \Gamma = \frac{\Gamma_i}{\left|1 - \frac{m v_{i\parallel} \sin^2 \vartheta}{\hbar k_{\parallel}}\right|} \equiv C \Gamma_i$
if $v_{i\parallel} < 0$, large; θ large; k_{\parallel} small
 $\rightarrow C < 1$, and $\Gamma < \Gamma_i$

The self-energy

It is useful to express the effects of the electron interactions in terms of the "electron self energy" defined as:

$$\Sigma(\mathbf{k},\omega) = \Sigma_1(\mathbf{k},\omega) + i\Sigma_2(\mathbf{k},\omega)$$

 $\Sigma(\mathbf{k},\omega)$: the *"self-energy"* - captures the effects of interactions

 $\Gamma = \Sigma_2 \qquad \qquad \mathbf{\epsilon}(\mathbf{k}) = \mathbf{\epsilon}_0(\mathbf{k}) + \Sigma_1(\mathbf{k}, \boldsymbol{\omega}) = Z_{\mathbf{k}} \mathbf{\epsilon}_0(\mathbf{k})$

$$Z_{k} = \left(1 - \frac{\partial \Sigma_{1}}{\partial \omega}\right)_{\omega = \varepsilon_{0}(k)}^{-1}$$

... rewriting $G(k,\omega)$ and $A(k,\omega)$:

$$G(k,\omega) = \frac{Z_K}{\omega - \left[\varepsilon_0(k) + \Sigma(k,\omega)\right]} + G_{inch.}(k,\omega)$$
$$A(k,\omega) = \frac{\Sigma_2}{\pi} \frac{Z_k}{\left[\omega - \varepsilon_0(k) - \Sigma_1\right]^2 + \Sigma_2^2} + A_{inch.}(k,\omega)$$

$$\lambda = \left(-\frac{\partial \Sigma_1}{\partial \omega}\right)_{\omega = E_F}$$

Coupling constant



→ energy renormalization: $E_{\vec{k}} = \varepsilon_{\vec{k}} + \operatorname{Re} \Sigma = Z_k \cdot \varepsilon_{\vec{k}}$ → lifetime broadening: $\Gamma_{\vec{k}} = \operatorname{Im} \Sigma$ → quasiparticle weight: $Z_{\vec{k}} = (1 - \frac{\partial \Sigma}{\partial \omega})^{-1} \leq 1$

The "Kinky" physics



electron + (dynamical) lattice polarization = polaronic quasiparticle

Electron-phonon coupling

λ-

$$A(k,\omega) = \frac{\Sigma_2}{\pi} \frac{Z_k}{\left[\omega - \varepsilon_0(k) - \Sigma_1\right]^2 + \Sigma_2^2} + A_{inch.}(k,\omega)$$

Spectral function: excitation spectrum

electronic self-energy

Im
$$\Sigma(\omega) \propto \int_0^{\omega} \alpha^2 F(\Omega) d\Omega = \lambda \int_0^{\omega} \rho_{ph}(\Omega) d\Omega$$

electron-phonon coupling constant

$Re\Sigma(\omega)$ from Kramers-Kronig relation

example: Einstein model:





$$\left|\varepsilon_{\vec{k}} - E_F\right| > \omega_0$$

hole emits (decays into) real phonon



$$\left|\varepsilon_{\vec{k}} - E_F\right| < \omega_0$$

hole emits and reabsorbs phonon, dressed with cloud of *virtual* phonons





example: Einstein model:



Debye Model (λ = 1)



theoretical energy distribution curves (EDCs)



Coupling to adsorbate vibrations on a surface

hydrogen adsorbed on W(110) – an Einstein-type system



E. Rotenberg, J. Schäfer et al., PRL 84, 2925 (2000)



W substrate

quantitative analysis:

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• energy scale: \omega_0 = 160 meV for H,
115 meV for D (isotope effect 1/\sqrt{2} )
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• coupling constant: $\lambda = 1.4$ for H/W(110)

- significant mass renormalization
- isotope effect $H \rightarrow D$ ($\omega_0 \sim 1/\sqrt{M}$)

Intrinsic electron-phonon coupling on a surface: Debye model



How to get λ ?: real part of Σ





Fig. 13. Dispersion (a) and MDC width (FWHM)(b) of LSCO samples ($x = 0.03 \sim 0.30$) measured along the nodal direction, as determined from fitting MDCs. For clarity, the dispersion in (a) is offset horizontally along the momentum axis. The green lines in (a) connect the points in dispersion at E_p and 0.2 eV which approximately represents the bare band; they also serve as guides to the eye to identify the kink in dispersion. The MDC width (b) shows an overall decrease with increasing doping. A slight drop in MDC width is discernible at a binding energy of ~80 meV, particularly obvious for lower doping samples.



but this may also be caused by something else

- yields directly λ when measured at 0 K.
- the effect has to be large in order to be observable
- the un-renormalized dispersion has to be known

How to get λ ?: imag. part of Σ

EDC linewidth
$$\Gamma = \Gamma_{e-e}(T) + \Gamma_{e-i}(T) + \Gamma_{e-ph}(T)$$

$$\Gamma_{e-ph}(T) = 2\pi\hbar \int_0^{\omega_m} d\omega' \alpha^2 F(\omega') [1 - f(\omega - \omega') + 2n(\omega') + f(\omega + \omega')] \simeq 2\pi\lambda k_{\rm B}T$$

- In most cases, the temperature dependence of the lifetime is dominated by the electron-phonon coupling.
- The T-dependence of the linewidth can be used to extract λ.
- The T-dependence is independent of binding energy (not too close to the Fermi level).
- several practical problems when the binding energy is very close to the Fermi level

$$\alpha^{2} F(\omega) = \lambda (\frac{\omega}{\omega_{D}})^{2} , \omega < \omega_{D}$$
$$\alpha^{2} F(\omega) = 0, \omega > \omega_{D}$$



B.A. McDougall, T. Balasubmaranian and E. Jensen PRB 51, 13891 (1995).

How to get λ ?: imag. part of Σ

EDC linewidth
$$\Gamma = \Gamma_{e-e} (\mathbf{X}) + \Gamma_{e-i} (\mathbf{X}) + \Gamma_{e-ph}(T)$$

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Electron-phonon coupling constant and superconductivity





Strong-coupling theory of superconductivity

	Matl	λ	w0 [K]	Tc(theory)	Tc(expt)
	W	0.28	390	0.01	0.012
	Мо	0.41	460	0.84	0.92
	Be	0.24	1000	0.02	0.026
3-D	Hg	1	72	3.56	4.16
	Pb	1.12	105	6.25	7.19
	Nb	0.82	277	9.20	9.22
	Pd	0.15	274	0.00	not SC
	PdH	0.75	475	12.67	10
2-D	H:W	0.5-1.4	1932	50-150	?
	Be surf	1.15	1000	70.21	?

$$T_c \propto \omega_0 \exp(-\frac{1}{\lambda})$$



kink observed in the cuprates :

- Cooper-pairing mediated by spin fluctuations ?
- problem: energy scales for phonons and magnetic modes very similar

Fe(001) surface state: dispersion and lifetime width





self-energy $\Sigma(\omega)$ derived from momentum distribution curves (MDCs)

peak maximum $\rightarrow \varepsilon_k + \operatorname{Re} \Sigma(\omega)$

renormalization @ 100-200 meV (>> $\omega_{\text{Debye}} \sim 30 \text{ meV}$)


1D System: breakdown of the Fermi liquid Spinon and holon dispersion



Distinct spinon and holon dispersions in photoemission spectral functions from one-dimensional SrCuO₂ B.J. Kim at al., Nature Physics 2 (2006)



t – hopping integral

U-local Coulomb energy

strong coupling U >> t

 $J \propto t^2/U$ - magnetic exchange energy





Figure 3 EDCs and dispersions. a, EDCs for k_{\parallel} between Γ and 0.6π at $k_{\perp} = 0.7 \text{ Å}^{-1}$. Each EDC is curve-fitted to find the peak positions. Two peaks were used in the region between $k_{\parallel} = \Gamma$ and $\pi/4$, whereas a single peak was used for the rest. The results are marked by red and blue circles. **b**, Experimental (symbols) and theoretical (solid and dashed lines) dispersions. The theoretical dispersions are obtained by taking the nearest-neighbour hopping of t = 0.65 eV and the exchange coupling of J = 0.23 eV. Dispersions from the band theory are also shown as two dotted lines²².

TTF-TCNQ: an organic 1D metal



1D axis

strongly anisotropic conductivity $\sigma_b/\sigma_a \approx \sigma_b/\sigma_c \sim 1000$

Peierls instability @ $T_p = 54$ K, incommensurate CDWs on TCNQ stacks

electronic correlation effects:

- 4k_F-fluctuations (on TTF stacks ?) observed up to 300 K
- enhanced magnetic susceptibility
- enhanced NMR relaxation rate
- ⇒ estimate for Hubbard model parameters:
 - $U \sim 4t \sim 1 eV$





1D System: breakdown of the Fermi liquid The Tomonaga-Luttinger liquid



SWCNTs: an example of Tomonaga-Luttinger liquid





Transition from a Tomonaga-Luttinger liquid to a Fermi liquid

 $n(E) \propto |E-E_F|^{\alpha}$, where $\alpha = (g+g^{-1}-2)/8$ depends on the size of the Coulomb interaction and g is the Luttinger parameter

 $\alpha \sim 0.53 \pm 0.05$ for pristine SWCNTs in agreement with other estimations

$\alpha = 0$ Fermi liquid





Mott-Hubbard insulator

Non-interacting Limit



- metallic
- bandwidth ~ 8t ~ 3 eV

Metal



Strongly Interacting (Mott) Limit

- insulating (Δ ~ 2 eV)
- antiferromagnetic
- bandwidth ~ 2*J* ~ 0.3 eV

Insulator



$Ca_{2-x}Na_{x}CuO_{2}Cl_{2}$: at x=0 Mott-Hubbard insulator



- Dispersion of peak intensity follows *t*-*J* model well
- Suggests quasiparticle excitations from t-J model are appropriate
- However, this is not the end of the story....



- Spectral function formalism FAILS to qualitatively describe lineshape
- Linewidth far too broad



• Vast majority of spectral weight in incoherent transitions

Ca_{2-x}Na_xCuO₂Cl₂: doping dependence



Ca_{2-x}Na_xCuO₂Cl₂: doping dependence





A. Goldoni, L. Sangaletti, S.L. Friedmann, Z.-X. Shen, M. Peloi, F. Parmigiani, G. Comelli and G. Paolucci, J. Chem. Phys. 113, 8266 (2000)

Fullerenes

Strongly correlated metal

Strong correlations U ~ 1 - 1.3 eV Small band dispersion W ~ 0.5 - 0.6 eV Orbital degeneracy (HOMO 5 fold, LUMO 3 fold) Small Fermi energy ~ 0.25 eV Phonon spectrum up to 0.2 eV Jahn-Teller distortions in charged C_{60} E_{JT} ~ 0.03-0.18 eV for C_{60}^{n-}

Mott-Hubbard insulator



ε_p

 $\epsilon_{d} \epsilon_{F}$





Band dispersion of K₃C₆₀(111)





Spectrum dominated by phonon and plasmon excitations; quasi-particle coherent peak confined near E_F



K₆C₆₀ (Ionic Crystal)

bcc lattice

LUMO bands completely filled: band insulator Ground state trivial

No molecular motion No J-T distortion No correlation effects No screening Coupling also to K⁺ modes





Photoemission creates a single hole in a full band, that couple to phonons ===> POLARON PROBLEM

Predictions for K₆C₆₀ (Ionic Crystal)



K⁺, C60⁶⁻ phonons are strongly coupled (g>> ω). ⇒ Smooth spectra (convolution with gaussian)

The width is dominated by the on-ball phonons.

- \Rightarrow The width is independent of the system
- \Rightarrow The width should be similar in K4C40 (?)

The first moment $\mu_1(k)$ in ARPES is the band structure. \Rightarrow The mean value of the broad peak should be kdependent.

What we should expect ?



S. Wehrli *et al.*, Phys. Rev. B **70**, 233412 (2004)

Band dispersion of K₆C₆₀(110)



Band dispersion of K₆C₆₀(110)



Band dispersion of K₆C₆₀(110)

At Γ the bandwidth due to the presence of the three LUMO bands should be very sharp and, even considering our integration in K₁, in the worst case we must expect a width of the photoemission feature of 0.25 eV => difference more than a factor of 2

Phonon contribution to the LUMO width





Temperature dependence of $K_6C_{60}(110)$ LUMO width at $\overline{\Gamma}$

$$FWHM = W_0 + 2\pi\hbar \int_0^{\omega_D} \alpha^2 F(\omega) [1 + 2n(\omega, T)] d\omega$$

 $\begin{array}{l} \textbf{Debye} \\ \textbf{Model} \end{array} \begin{cases} \alpha^{2} F(\omega) = [\lambda \omega / \sqrt{(\omega_{D}^{2} - \omega^{2})}] / \pi \text{ (2D model)} \\ \alpha^{2} F(\omega) = \lambda (\omega / \omega_{D})^{2} \text{ (3D model)} \end{cases}$

B. Hellsing et al., J. Phys.: Condens. Matter 14, 5959 (2002)



Calculations explain why the el-ph coupling leads to a broadening of spectra calculated by neglecting el-ph coupling, with minor influence on the dispersion. O. Rösch and O. Gunnarsson, Eur. Phys. J. B **43**, 11 (2005)

In the intermediate polaron regime the dispersion of the incoherent spectral function (that dominates the spectrum) is weakly affected compared to the weak-coupling regime (spectrum dominated by the coherent part and bear a close resemblance with the free-electron case), but with a much more broadened lineshape reflecting the stronger coupling to the phonon distribution. M. Hohenadler *et al.*, Phys. Rev. B **71**, 245111 (2005)



Similar results obtained for a Mott-Hubbard insulator with intermediate coupling to phonons S. Fratini and S. Ciuchi, PRB 72 235107 (2005)

Very low-energy photoemission spectroscopy

Andrea Goldoni Sincrotrone Trieste S.C.p.A.





- How low photon energy are produced
- The Bad ElPh beamline
- Reasons for low photon energy: bulk sensitivity, higher momentum resolution, good energy resolution easier
- Sudden Approx still valid?
- Final state effects?
- Other problems

How low photon energies can be obtained ?

1) Gas discharge lamp (He=21.22 eV, Ne=16.85 eV, Ar= 11.62-11.83 eV, H₂= 10.2 eV)

Large spot size (several mm), ~ 10^{14} photons/s, intrinsic linewidth ~ 1-2meV satellite lines







How low photon energies can be obtained ?

2) Laser systems (6 - 7 eV)

Spot size $1-500\mu m$, > 10^{15} photons/s on the sample, intrinsic linewidth 0.26-0.1meV, only one energy S. Shin, RIKEN, Tokyo Univ. (Jap)

> Schematic of a system for performing photoemission spectroscopy based on a frequency quadrupled Ti:sapphire oscillator (6 eV) running at 100 MHz.

Note the high repetition rate:

Needed for a high signal to noise while keeping the instantaneous electron emission rate low.

This last aspect is critical for keeping the electronic response of the sample in the linear regime and to minimize space-charge and other spurious effects. S. Shin, RIKEN, Tokyo Univ. (Jap) D.S. Dessau, Univ. Colorado (USA)



Laser excitation photoemission spectrometer



How low photon energies can be obtained ?

3) Synchrotron radiation

Spot size $10-400\mu$ m, > 10^{12} photons/s on the sample, intrinsic linewidth < 1meV, continuous energy range



BaD ElPh Layout 4m Normal Incidence Monochromator: 5°



Energy range: 5 - 23 eV with two gratings, a third grating foreseen for 23-35 eV

The monochromator performances

20 eV, resolving power 45000 (10 μ m) 12 eV, resolving power 75000 (10 μ m) 8 eV, resolving power 50000 (10 μ m)

Expected performances:

Cryostat/manipulator T ~ 4 K

Total energy resolution ~ 3 meV

Momentum resolution < 0.005 Å⁻¹

Actual performances:

Cryostat/manipulator T ~ 11 K (on the sample)

Total energy resolution ~ 5.7 meV

Momentum resolution < 0.005 Å⁻¹

GAMMADATA -SCIENTA-

Features:

- < 3 meV energy resolution</p>
- Angle multiplexing recording from small area samples
- Extremely low noise, high stability power supplies
- Customized lens design
- Multi-channel resistive anode detector

Main application:

- High resolution electron spectroscopy
- High resolution
 photo-electron diffractionion
- High resolution angular resolved spectroscopy

256x256 pixels128 slices (spectra)3 MHz count-rate

SCIENTA SES 50

Mounted on a two-axis goniometer

Courtesy of R. Claessen (Univ. of Wuerzburg)

- EF=5.03563; FWHM:5.8meV; T=164 K
- somma_vite 300K

- fit_somma_vite 300K

EF=5.0356; FWHM:5.8meV; T=300 K

A. Goldoni et al., unpublished

PE=2 eV

$$0.4$$

 0.4
 0.3
 0.3
 0.2
 0.1
 0.3
 0.3
 0.3
 0.3
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 θ range = 5° 21 slices; $\Delta \theta \sim 0.25^{\circ}$ $\Delta K < 0.005 \text{ Å}^{-1}$

Why going to very low photon energies? 4 eV < hv < 20 eV

Bulk sensitivity
 Higher momentum resolution
 Good energy resolution easier

Why going to very low photon energies? 4 eV < hv < 20 eV

1) Bulk sensitivity

2) Higher momentum resolution3) Good energy resolution easier

Electrons photoemitted with low photon energies are the most bulk sensitive

Superconducting gap of Nb



T. Kiss et al., JESRP 144-147, 953 (2005)

Fermi surface of Bi(111): Bulk vs Surface states





FIG. 4 (color). Band structure of Bi(111) at $h\nu = 18$ eV. k_{\parallel} along $\overline{\Gamma M}$. Solid lines: Polynomial fit to peak positions. Energies relative to chemical potential μ .

C.R. Ast, H. Hochst, PRL 87, 177602 (2001)





FIG. 1 (color). Intensity map at the Fermi level of Bi(111) measured at $h\nu = 18$ eV. The angular steps were 0.25°. k_x and k_y are the parallel components of the electron momentum along the $\overline{\Gamma M}$ and the $\overline{\Gamma K}$ direction, respectively.

C.R. Ast, H. Hochst, PRL 87, 177602 (2001)



- Momentum
- Distribution
- Curves at E_F for
- Bi(111) along the $\underline{\Gamma K}$

Note:

bulk states (BS) appear at low photon energies

C.R. Ast, H. Hochst, PRL 87, 177602 (2001)

Photoemission from Mg(0001): surface *vs* **bulk states**







Mott transition in V₂O₃

M. Marsi et al., submitted to PRB (similar experiment made by R. Claessen et al.)

 $(V_{1-x}Cr_x)_2O_3$ prototype system for isostructural metal-insulator transition induced by electron correlations

 $(V_{1-x}Cr_x)_2O_3 = x = 0.011$

T=300K paramagnetic insulator T=200K paramagnetic metal



Mott transition in V₂O₃



M. Marsi et al., submitted to PRB



Photoemission on BaD ElPh Low photon energy Normal emission

metallic phase shows larger difference between surface and bulk

Surface is more correlated than bulk

True also for other strongly correlated systems ?

Coronene ($C_{24}H_{12}$) on Au(110), intercalated with Rb



Petra Rudolf et al.



University of Groningen Zernike Institute for Advanced Materials



As the LUMO fills no states near E_F : always insulating

Plenty of similar photoemission examples in the literature: phtalocynins, porphyrins, ...



Rb-Coronene: Fermi region with hv < 10 eV



At hv = 9 eV the evolution is completely different: density of states crossing Fermi

The LUMO states are closer to Fermi and crosses E_F



University of Groningen Zernike Institute for Advanced Materials

Petra Rudolf et al.

Attenuation length of low electron in solids: CoO/Ag and C_{60} /Ag



Why going to very low photon energies? 4 eV < hv < 20 eV

Bulk sensitivity Higher momentum resolution



Kinematic relations

$$k_{out} = \sqrt{\frac{2m}{\hbar^2}} E_{kin}$$
$$k_{in} = \sqrt{\frac{2m}{\hbar^2}} (E_{kin} + V_0)$$
$$k_{out,\parallel} = k_{in,\parallel} \equiv k_{\parallel}$$

"Snell's Law"

$$k_{\parallel} = \sin \theta_{out} \sqrt{\frac{2m}{\hbar^2} E_{kin}} = \sin \theta_{in} \sqrt{\frac{2m}{\hbar^2} (E_{kin} + V_0)}$$

Critical angle for emission

$$(\sin \theta_{out})_{\max} = \sqrt{\frac{E_{kin}}{E_{kin} + V_0}}$$

At the surface the crystal symmetry is conserved in the surface plane but is broken perpendicularly to the surface: the component of the electron momentum parallel to the surface plane $(k_{//})$ is conserved, but k_{\perp} is not

$$k_{//} = \sqrt{\frac{2m^* E_k}{\hbar^2}} \sin \theta_{out} \approx 0.512 \sqrt{E_k} \sin \theta_{out}$$

The angular resolution is defined by the electron energy analyzer. Suppose it is 0.5° and the BZ boundary is ~ 0.25 Å⁻¹.

At $E_k=25 \text{ eV}$ the BZ boundary is reached after ~ 5.5° We have 11 sampling points $\rightarrow \Delta k_{//} \sim 0.025 \text{ Å}^{-1}$

At $E_k=9 \text{ eV}$ the BZ boundary is reached after ~ 9.5° We have 19 sampling points $\rightarrow \Delta k_{//} \sim 0.014 \text{ Å}^{-1}$

GOOD for systems with small **BZ**

Example: Band structure in fullerides

Typical hexagonal surface lattice parameter > 10 Å



Measured at 22 eV. Lower photon energy should allow better Fermi surface mapping.

W. Yang et al., Science **300**, 303 (2003);V. Brouet et al., PRL (2004)



Why going to very low photon energies? 4 eV < hv < 20 eV

Bulk sensitivity Higher momentum resolution

3) Good energy resolution easier



T. Kiss et al., JESRP 144-147, 953 (2005)

Angle Resolved Photoemission Spectroscopy of MgB₂ Single Crystals



s and **p** superconducting gaps

"sub meV" resolution spectra on MgB₂ by laser-PES



Superconducting gap of CeRu₂



Superconducting gap was clearly observed by laser-PES Kiss et al., PRL 94 (2005)57001

Pseudo-gap opening in FeSi



Critical question for ARPES at such low energies: is the Sudden Approx still valid?

Fermi's Golden Rule for *N*-particle states:

$$I(\vec{k},\varepsilon) \propto \sum_{s} \left| \left\langle \Psi_{f,s} \left| \hat{\Delta} \right| \Psi_{i,0} \right\rangle \right|^{2} \delta(E_{N,s} - E_{N,0} - h\nu)$$

SUDDEN APPROXIMATION:

$$|\Psi_{f,s}\rangle = |\vec{k}, N-1, s\rangle = c_{\vec{k}}^{+}|N-1, s\rangle$$
 Factorization !
photoelectron stheigenstate of remaining N-1 electron system

<u>Physical meaning</u>: photoelectron decouples from remaining system immediately after photoexcitation, *before* relaxation sets in This is the most important result: in the sudden approx. the photoemission spectrum is proportional to the single particle spectral density function $A(k, \omega)$



The single particle spectral function $A(k, \omega)$ gives the probability that the original system plus the bare hole (electron suddenly removed) will be found in an exact eigenstate of the (N-1)-system



non-interacting system

$$A(k,\omega) = -\frac{1}{\pi} \operatorname{Im} G(k,\omega) = \frac{\Gamma}{\pi} \frac{\left| \langle N - 1, i | c_k | N, i \rangle \right|^2}{\left(\omega - \varepsilon(k) \right)^2 + \Gamma^2} = \frac{\Gamma}{\pi} \frac{1}{\left(\omega - \varepsilon_0(k) \right)^2 + \Gamma^2}$$

interacting system

Ô

$$+ \mathbf{A}(k,\omega) = -\frac{1}{\pi} \operatorname{Im} G(k,\omega) = \frac{\Gamma}{\pi} \frac{|\langle N-1,i|c_k|N,i\rangle|^2}{(\omega - \varepsilon(k))^2 + \Gamma^2} + \frac{\Gamma}{\pi} \sum_{s \neq i} \frac{|\langle N-1,s|c_k|N,i\rangle|^2}{(\omega - \varepsilon_s(k))^2 + \Gamma^2}$$

$$= A(k,\omega)_{\operatorname{coh.}} + A(k,\omega)_{\operatorname{incoh}}$$



$$A(k,\omega) = \frac{\Gamma}{\pi} \frac{Z_k}{(\omega - \varepsilon(k))^2 + \Gamma^2} + \frac{\Gamma}{\pi} \sum_{s \neq i} \frac{\left| \langle N - 1, s | c_k | N, i \rangle \right|^2}{(\omega - \varepsilon_s(k))^2 + \Gamma^2} = A(k,\omega)_{\text{coh.}} + A(k,\omega)_{\text{incoh}}$$



Debye Model ($\lambda = 1$)



$$\operatorname{Im}\Sigma(\omega) \propto \lambda \int_0^{\omega} \rho_{phonon}(\Omega) d\Omega$$

energy scale Ω_{phonon} :

separates between virtual and real scattering processes

coupling constant λ :

effective Fermi velocity $v_F^* = v_F^{\theta} / (1 + \lambda)$

effective mass $m^* = (1+\lambda)m_{\theta}$

i.e.
$$Z = (1+\lambda)^{-1}$$



No dramatic changes in the electronic spectra near the Fermi surface. The sudden approx seems to be still valid or its breakdown may be not so important for the states near E_F .

Another critical point for ARPES at low energies: "Final state" effects











HOMO dispersion apparently smaller than at 8 eV, but of the order of 0.2 eV ($K_{\prime\prime\prime}$ integration? Final state effects?)



C₆₀(111) multilayer



inverse photoemission







 \rightarrow CaVO₃ more strongly correlated metal than SrVO₃?



Ca_{1-x}Sr_xVO₃: angle-*integrated* photoemission



- \Rightarrow at surface: reduced atomic coordination
- \Rightarrow effective bandwidth smaller:

$$W_{surf} < W_{bulk}$$

- \Rightarrow surface stronger correlated: $U/W_{surf} > U/W_{bulk}$
- \Rightarrow surface effect stronger for CaVO₃, but in bulk ~ identical for all compositions





Good agreement, everything seems understood


Sekiyama, PRL(2004)

scaled down by a factor of 0.6.

3d partial density of states but the energy is



Other problems:

- Magnetic fields must be screened very well
- The total reflection angle for bulk state emission can be reached



• Large Brillouin zones cannot be mapped completely

SPIN POLARIZATION: HOW TO MEASURE and SOME EXAMPLES





Gold foil is used because of its high Z, it is non-reactive and because thin gold, films which reduce multiple scattering, are easy to produce.

The presence of a spin-orbit term in the scattering potential introduces a spin dependence in the scattering cross section. Two detectors at exactly the same scattering angle to the left and right of the foil count the number of scattered electrons. $\rho\hbar^2 = 1 \ \partial V$









J. Osterwalder et al, (2005)





Rashba-Spin-Orbit Effect at Metal Surface States

J. Osterwalder et al, (2005)





Schematic diagram of near-gap optical transition for circularly polarized light



$$P = \frac{\left| I \downarrow -I \uparrow \right|}{\left| I \downarrow +I \uparrow \right|}$$

$$I = \left| \left\langle \Psi_f \left| H_{\text{int}} \right| \Psi_i \right\rangle \right|^2$$

$${H_{\mathrm{int}}} = X + i Y$$
 for $\sigma^{\scriptscriptstyle +}$ light

Ideal material for SPES application

- Direct band gap
- Large spin-orbit splitting
- Large and positive crystal field splitting

Crystal Field splitting: Compressive strain in GaAs P. Saez et al, IEEE (1996)



PES of GaAs and GaAs-based materials

• Advantages:

♦ moderate even high polarization: *P* ~90% @ QE 0.5%

♦ high brightness: 10⁵ A/cm² • sr

♦ good beam quality: small energy spreading etc.

Polarization direction can be easily changed by reversing the helicity of the incident light

• Disadvantages:

P is only 20— 35% for bulk GaAs
low QE for strained superlattice GaAs-based material
Cs and O₂ activation to get "negative electron affinity" every hundreds of hours